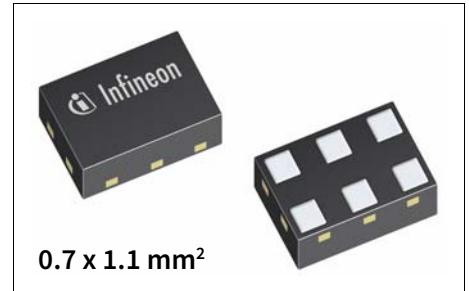


BGA855N6

Low Noise Amplifier for Lower L-Band GNSS Applications

Features

- Operating frequencies: 1164 - 1300 MHz
- Insertion power gain: 17.8dB
- Low noise figure: 0.60 dB
- High linearity performance IIP3: 0 dBm
- Low current consumption: 4.8 mA
- Ultra small TSNP-6-10 leadless package (footprint: 0.7 x 1.1 mm²)
- RF output internally matched to 50 Ohm
- Only one external matching component needed
- Specifically designed for:
 - L2/L5 GPS Signals
 - E5a/E5b/E6 Galileo Signals
 - G2/G3 Glonass Signals
 - B2/B3 Beidou Signals



Application

The BGA855N6 is designed to enhance GNSS signal sensitivity for band L2/L5 especially for very high accuracy. Besides GPS L5 and L2, the GNSS LNA also covers Galileo E5a, E5b, E6, Glonass G3, G2 and Beidou B3 and B2 bands. The high linearity performance of BGA855N6 ensures best sensitivity for the operation in 4G & 5G NSA configurations.

Product Validation

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

Block diagram

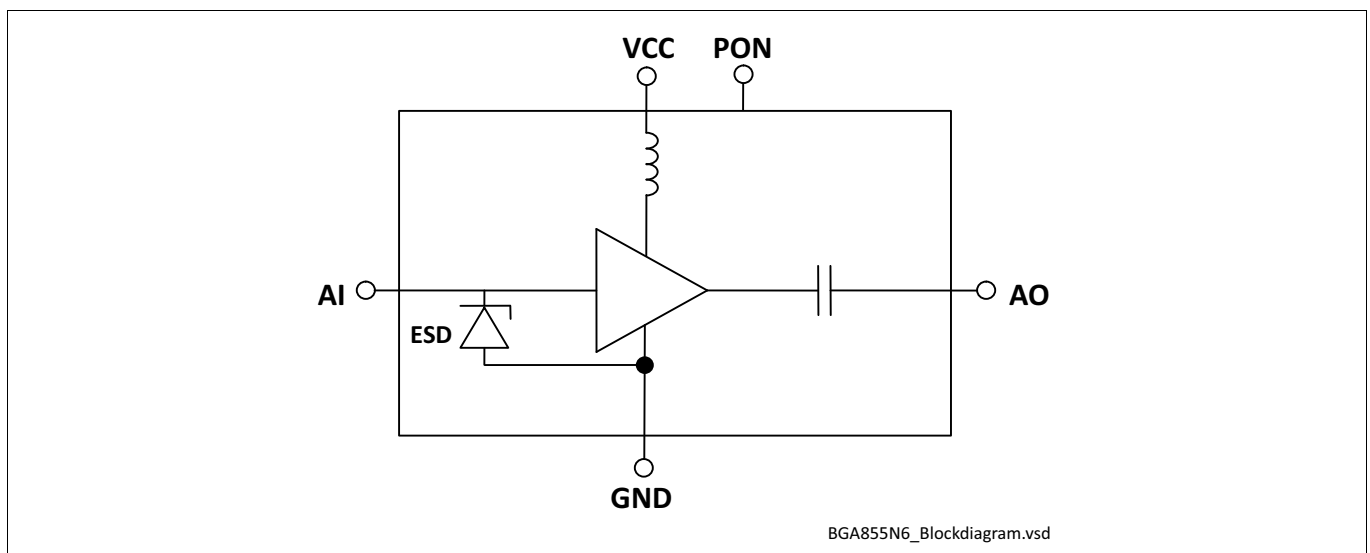




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Features

1 Features

- Insertion power gain: 17.8 dB
- Low noise figure: 0.60 dB
- Low current consumption: 4.8 mA
- High linearity performance IIP3: 0 dBm
- Operating frequencies: 1164 - 1300 MHz
- Supply voltage: 1.1 V to 3.3 V
- Ultra small TSNP-6-10 leadless package (footprint: 0.7 x 1.1 mm²)
- B9HF Silicon Germanium technology
- RF output internally matched to 50 Ohm
- Only one external matching component needed
- 2kV HBM ESD protection (including AI-pin)
- Pb-free (RoHS compliant) package
- Specifically designed for:
 - L2/L5 GPS Signals
 - E5a/E5b/E6 Galileo Signals
 - G2/G3 Glonass Signals
 - B2/B3 Beidou Signals

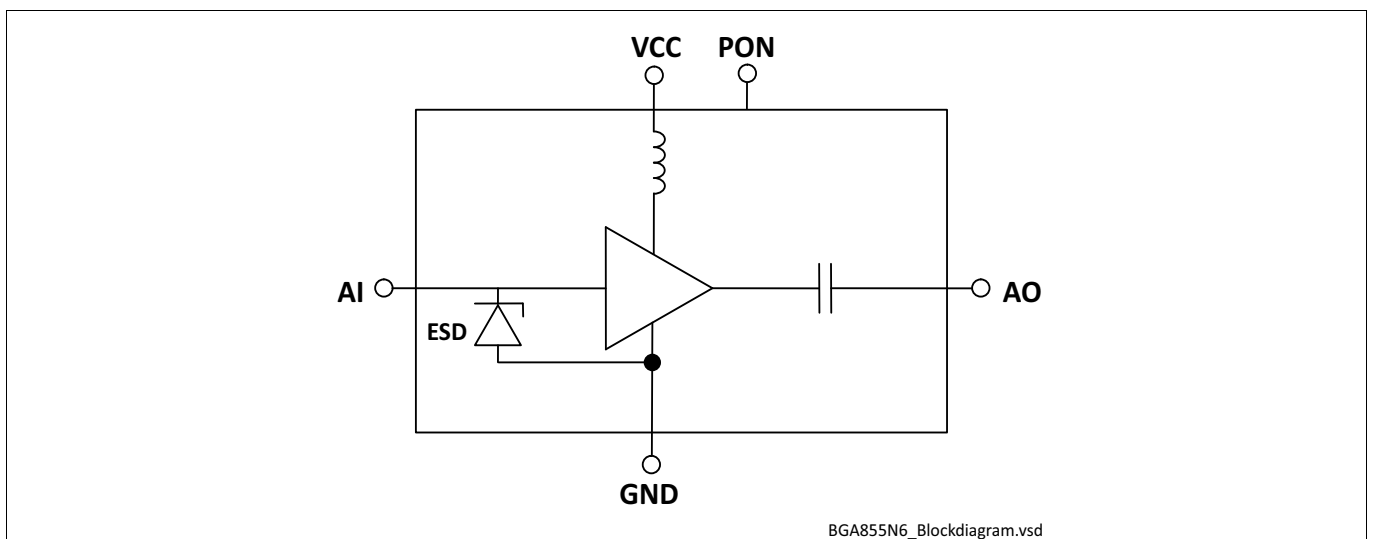


Figure 1 Block Diagram

| Product Name | Marking | Package |
|--------------|---------|-----------|
| BGA855N6 | 6 | TSNP-6-10 |

Features

Description

The BGA855N6 is a front-end low noise amplifier for GPS L5 and L2, Galileo E5a, E5b, E6, Glonass G3, G2 and Beidou B3 and B2 bands for a frequency range from 1164 MHz to 1300 MHz. The LNA provides 17.8 dB gain and 0.60 dB noise figure at a current consumption of 4.8 mA in the application configuration described in [Chapter 4](#). The BGA855N6 is based upon Infineon Technologies' B9HF Silicon Germanium technology. It operates from 1.1 V to 3.3 V supply voltage (device optimized for 1.8V operation / also prepared to support 1.2V and 2.8V operation). OFF-state can be enabled by PON pin.

Pin Definition and Function

Table 1 Pin Definition and Function

| Pin No. | Name | Function |
|----------------|-------------|------------------|
| 1 | GND | Ground |
| 2 | VCC | DC supply |
| 3 | AO | LNA output |
| 4 | GND | Ground |
| 5 | AI | LNA input |
| 6 | PON | Power On Control |

Maximum Ratings

2 Maximum Ratings

Table 2 Maximum Ratings

| Parameter | Symbol | Values | | | Unit | Note or Test Condition |
|--|----------------|--------|------|----------------|------|------------------------|
| | | Min. | Typ. | Max. | | |
| Voltage at pin VCC ¹⁾ | V_{CC} | -0.3 | – | 3.6 | V | – |
| Voltage at pin AI | V_{AI} | -0.3 | – | 0.9 | V | – |
| Voltage at pin AO | V_{AO} | -0.3 | – | $V_{CC} + 0.3$ | V | – |
| Voltage at pin PON | V_{PON} | -0.3 | – | $V_{CC} + 0.3$ | V | – |
| Voltage at pin GND | V_{GND} | -0.3 | – | 0.3 | V | – |
| Current into pin VCC | I_{CC} | – | – | 16 | mA | – |
| RF input power | P_{IN} | – | – | +25 | dBm | – |
| Total power dissipation, $T_S < 148\text{ °C}^2)$ | P_{tot} | – | – | 60 | mW | – |
| Junction temperature | T_J | – | – | 150 | °C | – |
| Ambient temperature range | T_A | -40 | – | 85 | °C | – |
| Storage temperature range | T_{STG} | -55 | – | 150 | °C | – |
| ESD capability all pins, HBM ³⁾ | V_{ESD_HBM} | -2000 | – | +2000 | V | – |

1) All voltages refer to GND-Node unless otherwise noted

2) T_S is measured on the ground lead at the soldering point

3) Human Body Model ANSI/ESDA/JEDEC JS-001 ($R = 1.5\text{k}\Omega$, $C = 100\text{pF}$)

Attention: *Stresses above the max. values listed here may cause permanent damage to the device. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit. Exposure to conditions at or below absolute maximum rating but above the specified maximum operation conditions may affect device reliability and life time. Functionality of the device might not be given under these conditions.*

Electrical Characteristics

3 Electrical Characteristics

Table 3 Electrical Characteristics $V_{CC} = 1.2V^{1)}$
 $T_A = 25\text{ }^{\circ}\text{C}$, $V_{CC} = 1.2\text{ V}$, $V_{PON} = 1.2\text{ V}$, $f = 1164 - 1300\text{ MHz}$

| Parameter | Symbol | Values | | | Unit | Note or Test Condition |
|---|----------------|--------|------|----------|---------------|---|
| | | Min. | Typ. | Max. | | |
| Supply voltage | V_{CC} | 1.1 | 1.2 | 3.3 | V | – |
| Supply current | I_{CC} | – | 4.4 | 5.4 | mA | ON Mode |
| | | – | 0.2 | 3 | μA | OFF Mode |
| Power on voltage | V_{PON} | 0.8 | – | V_{CC} | V | ON Mode |
| | | 0 | – | 0.4 | V | OFF Mode |
| Supply current | I_{PON} | – | 1.5 | 3 | μA | ON Mode |
| | | – | – | 1 | μA | OFF Mode |
| Insertion power gain $f = 1214\text{ MHz}$ | $ S_{21} ^2$ | 16.6 | 17.6 | 18.6 | dB | – |
| Noise figure ²⁾ $f = 1214\text{ MHz}$, $Z_S = 50\ \Omega$ | NF | – | 0.60 | 1.10 | dB | – |
| Input return loss ³⁾ $f = 1214\text{ MHz}$ | RL_{IN} | 8 | 11 | – | dB | – |
| Output return loss ³⁾ $f = 1214\text{ MHz}$ | RL_{OUT} | 12 | 20 | – | dB | – |
| Reverse isolation ³⁾ $f = 1214\text{ MHz}$ | $1/ S_{12} ^2$ | 19 | 22 | – | dB | – |
| Power on time ⁴⁾⁷⁾ | t_S | – | 3 | 5 | μs | OFF to ON Mode |
| Inband input 1dB-compression point, $f = 1214\text{ MHz}^{3)}$ | IP_{1dB} | -18 | -14 | – | dBm | – |
| Inband input 3 rd -order intercept point ³⁾⁵⁾ $f_1 = 1214\text{ MHz}$, $f_2 = f_1 \pm 1\text{ MHz}$ | IIP_3 | -6 | -1 | – | dBm | – |
| Out of band input 3 rd -order intercept point ⁶⁾⁷⁾ $f_1 = 1850\text{ MHz}$, $f_2 = 2500\text{ MHz}$ | IIP_{300B} | -4 | 1 | – | dBm | – |
| Stability ⁷⁾ | k | > 1 | – | – | | $f = 20\text{ MHz} \dots 10\text{ GHz}$ |

1) Based on the application described in [Chapter 4](#)

2) PCB losses are subtracted

3) Verification based on AQL; not 100% tested in production

4) LNA Gain changed to 90% of final gain value (in dB)

5) Input power = -30 dBm for each tone

6) Input power = -25 dBm for each tone

7) Guaranteed by device design; not tested in production

Electrical Characteristics

Table 4 Electrical Characteristics $V_{CC} = 1.8V$ ¹⁾ $T_A = 25\text{ }^\circ\text{C}$, $V_{CC} = 1.8\text{ V}$, $V_{PON} = 1.8\text{ V}$, $f = 1164 - 1300\text{ MHz}$

| Parameter | Symbol | Values | | | Unit | Note or Test Condition |
|---|----------------|--------|------|----------|---------------|---|
| | | Min. | Typ. | Max. | | |
| Supply voltage | V_{CC} | 1.1 | 1.8 | 3.3 | V | – |
| Supply current | I_{CC} | – | 4.8 | 5.8 | mA | ON Mode |
| | | – | 0.2 | 3 | μA | OFF Mode |
| Power on voltage | V_{PON} | 0.8 | – | V_{CC} | V | ON Mode |
| | | 0 | – | 0.4 | V | OFF Mode |
| Supply current | I_{PON} | – | 2.5 | 7.5 | μA | ON Mode |
| | | – | – | 1 | μA | OFF Mode |
| Insertion power gain $f = 1214\text{ MHz}$ | $ S_{21} ^2$ | 16.8 | 17.8 | 18.8 | dB | – |
| Noise figure ²⁾ $f = 1214\text{ MHz}$, $Z_S = 50\ \Omega$ | NF | – | 0.60 | 1.10 | dB | – |
| Input return loss ³⁾ $f = 1214\text{ MHz}$ | RL_{IN} | 9 | 12 | – | dB | – |
| Output return loss ³⁾ $f = 1214\text{ MHz}$ | RL_{OUT} | 12 | 20 | – | dB | – |
| Reverse isolation ³⁾ $f = 1214\text{ MHz}$ | $1/ S_{12} ^2$ | 19 | 22 | – | dB | – |
| Power on time ⁴⁾⁷⁾ | t_S | – | 3 | 5 | μs | OFF to ON Mode |
| Inband input 1dB-compression point, $f = 1214\text{ MHz}$ ³⁾ | IP_{1dB} | -15 | -11 | – | dBm | – |
| Inband input 3 rd -order intercept point ³⁾⁵⁾ $f_1 = 1214\text{ MHz}$, $f_2 = f_1 \pm 1\text{ MHz}$ | IIP_3 | -5 | 0 | – | dBm | – |
| Out of band input 3 rd -order intercept point ⁶⁾⁷⁾ $f_1 = 1850\text{ MHz}$, $f_2 = 2500\text{ MHz}$ | IIP_{3OoB} | -4 | 1 | – | dBm | – |
| Stability ⁷⁾ | k | > 1 | – | – | | $f = 20\text{ MHz} \dots 10\text{ GHz}$ |

1) Based on the application described in [Chapter 4](#)

2) PCB losses are subtracted

3) Verification based on AQL; not 100% tested in production

4) LNA Gain changed to 90% of final gain value (in dB)

5) Input power = -30 dBm for each tone

6) Input power = -25 dBm for each tone

7) Guaranteed by device design; not tested in production

Electrical Characteristics

Table 5 Electrical Characteristics $V_{CC} = 2.8V$ ¹⁾ $T_A = 25\text{ }^\circ\text{C}$, $V_{CC} = 2.8\text{ V}$, $V_{PON} = 2.8\text{ V}$, $f = 1164 - 1300\text{ MHz}$

| Parameter | Symbol | Values | | | Unit | Note or Test Condition |
|---|----------------|--------|------|----------|---------------|---|
| | | Min. | Typ. | Max. | | |
| Supply voltage | V_{CC} | 1.1 | 2.8 | 3.3 | V | – |
| Supply current | I_{CC} | – | 5.4 | 6.4 | mA | ON Mode |
| | | – | 0.2 | 3 | μA | OFF Mode |
| Power on voltage | V_{PON} | 0.8 | – | V_{CC} | V | ON Mode |
| | | 0 | – | 0.4 | V | OFF Mode |
| Supply current | I_{PON} | – | 5 | 10 | μA | ON Mode |
| | | – | – | 1 | μA | OFF Mode |
| Insertion power gain $f = 1214\text{ MHz}$ | $ S_{21} ^2$ | 16.9 | 17.9 | 18.9 | dB | – |
| Noise figure ²⁾ $f = 1214\text{ MHz}$, $Z_S = 50\ \Omega$ | NF | – | 0.60 | 1.10 | dB | – |
| Input return loss ³⁾ $f = 1214\text{ MHz}$ | RL_{IN} | 10 | 13 | – | dB | – |
| Output return loss ³⁾ $f = 1214\text{ MHz}$ | RL_{OUT} | 12 | 20 | – | dB | – |
| Reverse isolation ³⁾ $f = 1214\text{ MHz}$ | $1/ S_{12} ^2$ | 19 | 22 | – | dB | – |
| Power on time ⁴⁾⁷⁾ | t_S | – | 3 | 5 | μs | OFF to ON Mode |
| Inband input 1dB-compression point, $f = 1214\text{ MHz}$ ³⁾ | IP_{1dB} | -12 | -8 | – | dBm | – |
| Inband input 3 rd -order intercept point ³⁾⁵⁾ $f_1 = 1214\text{ MHz}$, $f_2 = f_1 \pm 1\text{ MHz}$ | IIP_3 | -4 | 1 | – | dBm | – |
| Out of band input 3 rd -order intercept point ⁶⁾⁷⁾ $f_1 = 1850\text{ MHz}$, $f_2 = 2500\text{ MHz}$ | IIP_{3OoB} | -3 | 2 | – | dBm | – |
| Stability ⁷⁾ | k | > 1 | – | – | | $f = 20\text{ MHz} \dots 10\text{ GHz}$ |

1) Based on the application described in [Chapter 4](#)

2) PCB losses are subtracted

3) Verification based on AQL; not 100% tested in production

4) LNA Gain changed to 90% of final gain value (in dB)

5) Input power = -30 dBm for each tone

6) Input power = -25 dBm for each tone

7) Guaranteed by device design; not tested in production

Application Information

4 Application Information

Application Board Configuration

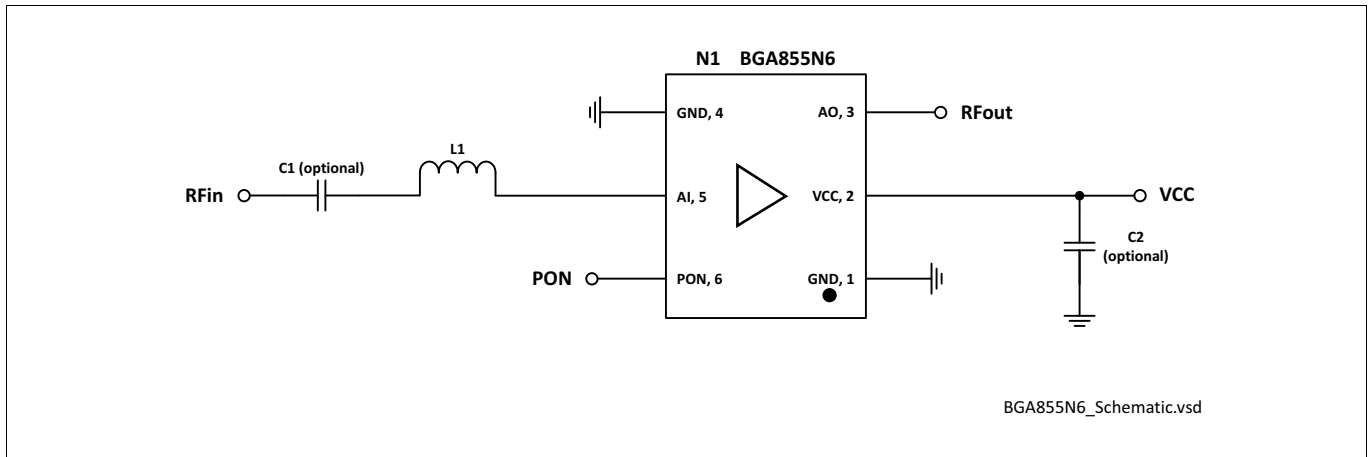


Figure 2 Application Schematic BGA855N6

Table 6 Bill of Materials

| Name | Value | Package | Manufacturer | Function |
|---------------|----------|-----------|-------------------|-------------------------|
| C1 (optional) | 1nF | 0402 | Various | Input matching |
| C2 (optional) | ≥ 1nF | 0402 | Various | RF bypass ¹⁾ |
| L1 | 9.4nH | 0402 | Murata LQW15 type | Input matching |
| N1 | BGA855N6 | TSNP-6-10 | Infineon | SiGe LNA |

1) RF bypass recommended to mitigate power supply noise

5 Package Information

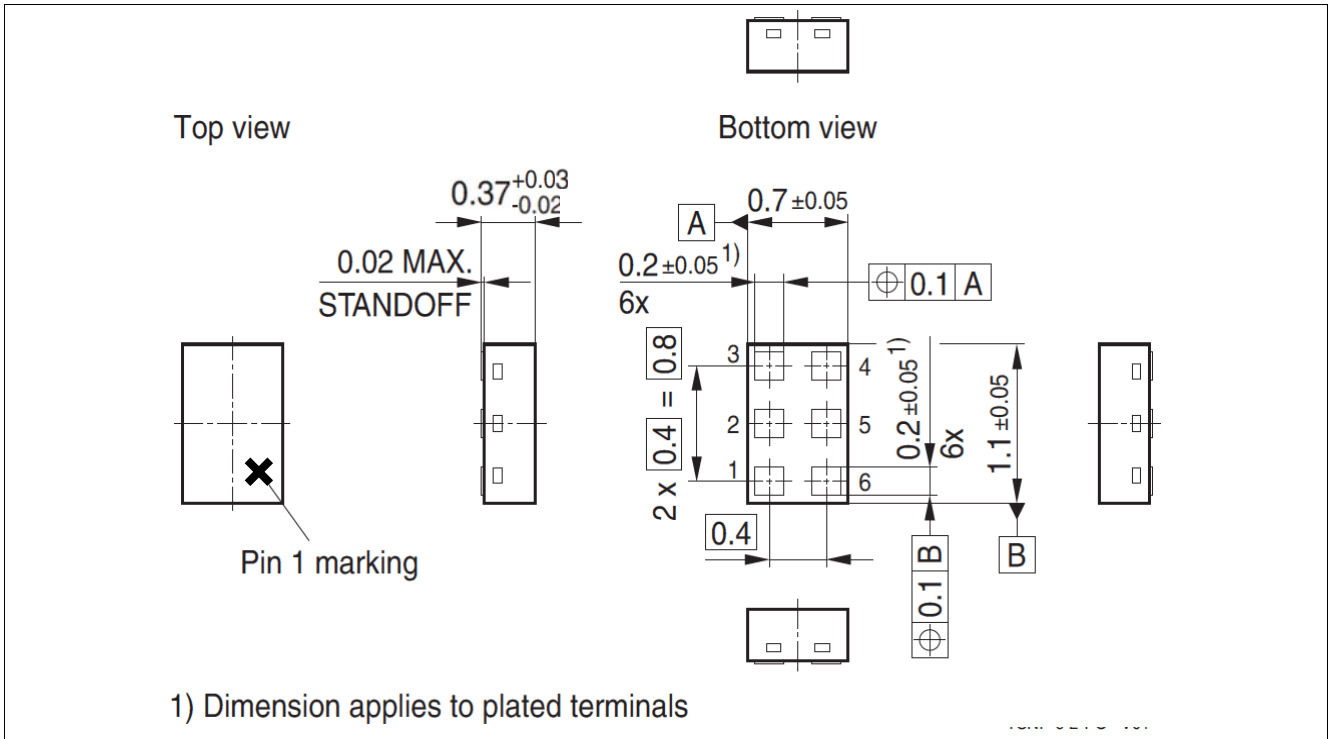


Figure 3 TSNP-6-10 Package Outline (top, side and bottom views)

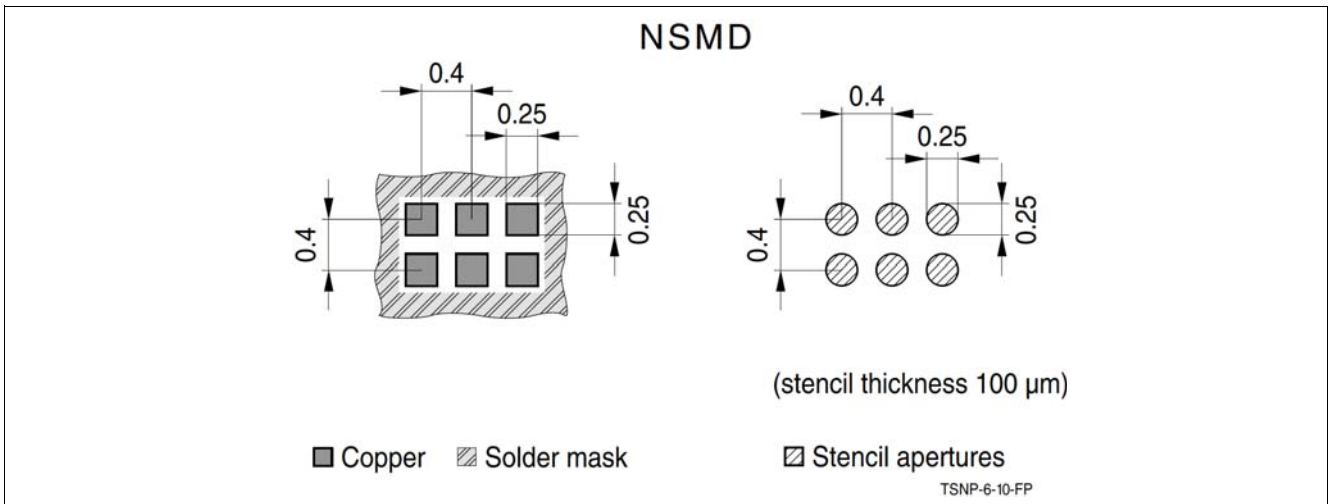


Figure 4 Footprint Recommendation TSNP-6-10

Package Information

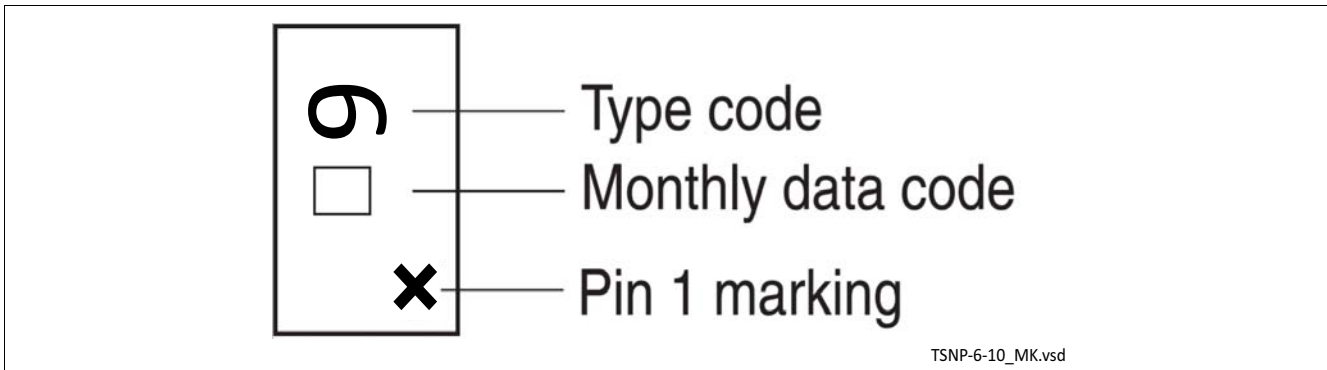


Figure 5 Marking Layout TSNP-6-10 (top view)

| Month | 2015 | 2016 | 2017 | 2018 | 2019 | 2020 | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 |
|-------|------|------|------|------|------|------|------|------|------|------|------|------|
| 01 | a | p | A | P | a | p | A | P | a | p | A | P |
| 02 | b | q | B | Q | b | q | B | Q | b | q | B | Q |
| 03 | c | r | C | R | c | r | C | R | c | r | C | R |
| 04 | d | s | D | S | d | s | D | S | d | s | D | S |
| 05 | e | t | E | T | e | t | E | T | e | t | E | T |
| 06 | f | u | F | U | f | u | F | U | f | u | F | U |
| 07 | g | v | G | V | g | v | G | V | g | v | G | V |
| 08 | h | x | H | X | h | x | H | X | h | x | H | X |
| 09 | j | y | J | Y | j | y | J | Y | j | y | J | Y |
| 10 | k | z | K | Z | k | z | K | Z | k | z | K | Z |
| 11 | l | 2 | L | 4 | l | 2 | L | 4 | l | 2 | L | 4 |
| 12 | n | 3 | N | 5 | n | 3 | N | 5 | n | 3 | N | 5 |

Figure 6 Date Code Marking TSNP-6-10

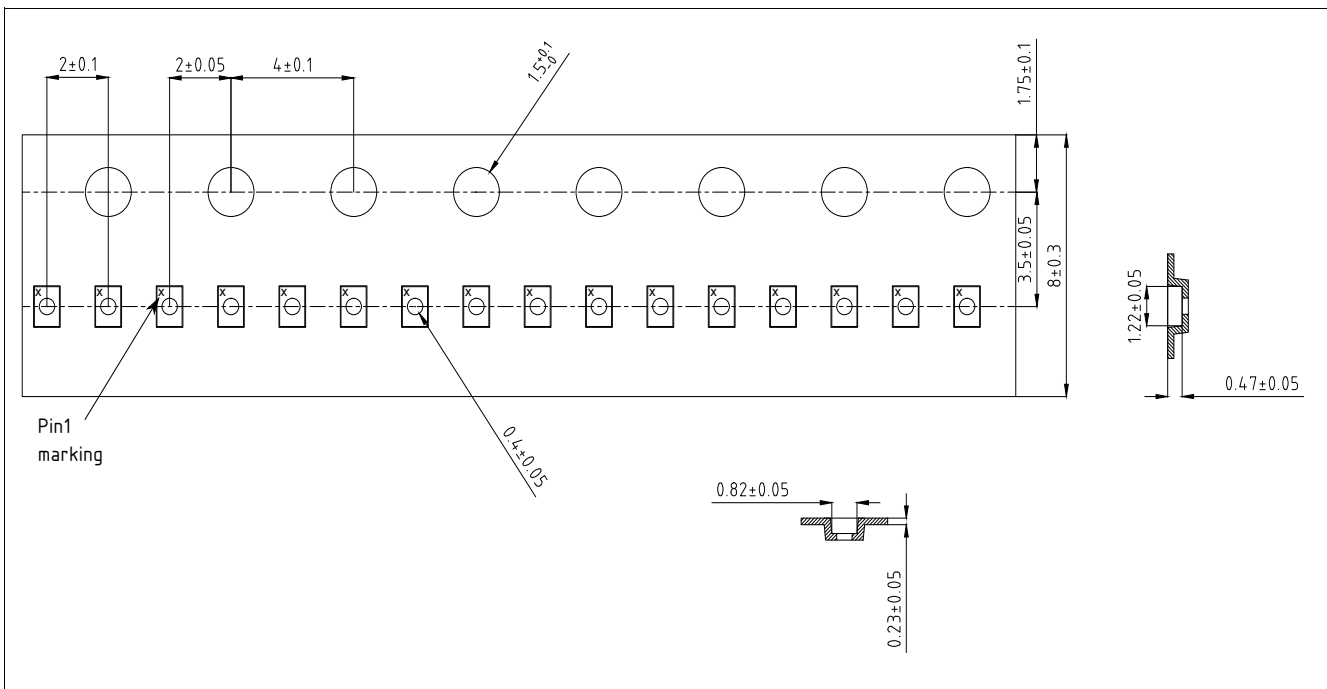


Figure 7 Tape & Reel Dimensions TSNP-6-10 (reel diameter 180 mm, pieces/reel 12000)

Revision History

| Page or Item | Subjects (major changes since previous revision) |
|---------------------------------|---|
| Revision 2.1, 2023-01-11 | |
| 6-8 | Update Power On Voltage for On Mode |
| | |
| | |

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